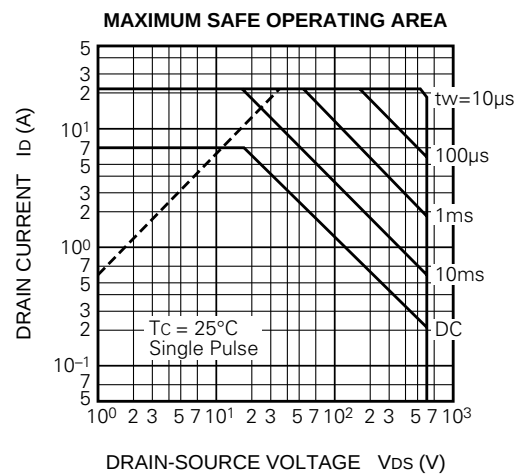
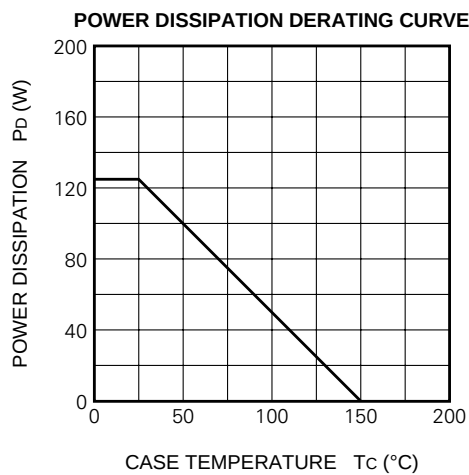


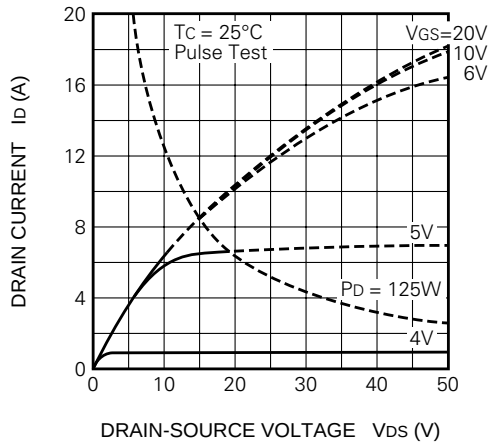
ELECTRICAL CHARACTERISTICS (T_{ch} = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V (BR) DSS	Drain-source breakdown voltage	I _D = 1mA, V _{GS} = 0V	600	—	—	V
V (BR) GSS	Gate-source breakdown voltage	I _G = ±100μA, V _{DS} = 0V	±30	—	—	V
I _{GSS}	Gate-source leakage current	V _{GS} = ±25V, V _{DS} = 0V	—	—	±10	μA
I _{DSS}	Drain-source leakage current	V _{DS} = 600V, V _{GS} = 0V	—	—	1	mA
V _{GS} (th)	Gate-source threshold voltage	I _D = 1mA, V _{DS} = 10V	2	3	4	V
r _{DS} (ON)	Drain-source on-state resistance	I _D = 3A, V _{GS} = 10V	—	1.25	1.63	Ω
V _{DS} (ON)	Drain-source on-state voltage	I _D = 3A, V _{GS} = 10V	—	3.75	4.89	V
y _{fs}	Forward transfer admittance	I _D = 3A, V _{DS} = 10V	3.3	5.5	—	S
C _{iss}	Input capacitance	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz	—	1100	—	pF
C _{oss}	Output capacitance		—	125	—	pF
C _{rss}	Reverse transfer capacitance		—	17	—	pF
t _d (on)	Turn-on delay time	V _{DD} = 200V, I _D = 3A, V _{GS} = 10V, R _{GEN} = R _{GS} = 50Ω	—	30	—	ns
t _r	Rise time		—	30	—	ns
t _d (off)	Turn-off delay time		—	100	—	ns
t _f	Fall time		—	35	—	ns
V _{SD}	Source-drain voltage	I _S = 3A, V _{GS} = 0V	—	1.5	2.0	V
R _{th} (ch-c)	Thermal resistance	Channel to case	—	—	1.00	°C/W
t _{rr}	Reverse recovery time	I _S = 7A, di _s /dt = -100A/μs	—	—	150	ns

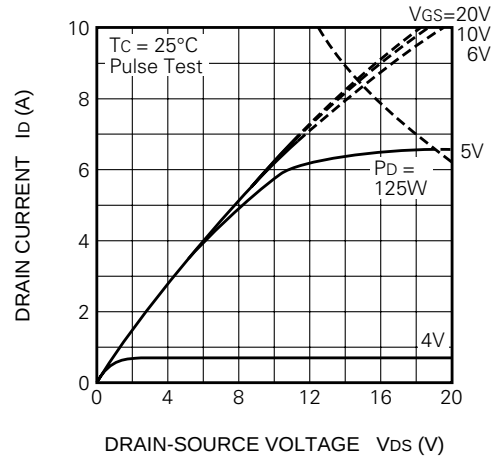
PERFORMANCE CURVES



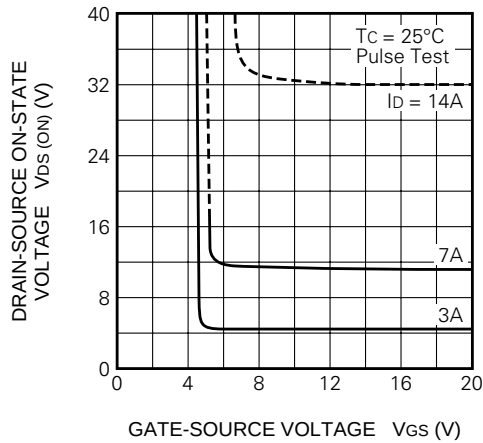
OUTPUT CHARACTERISTICS
(TYPICAL)



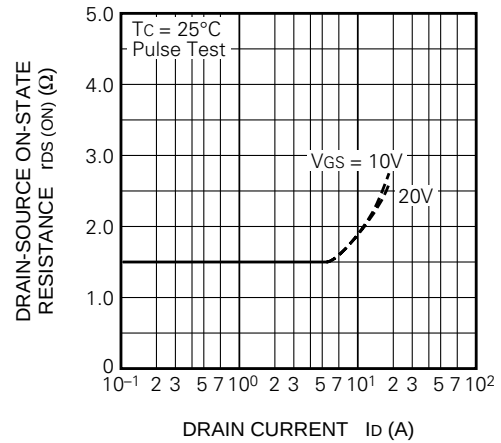
OUTPUT CHARACTERISTICS
(TYPICAL)



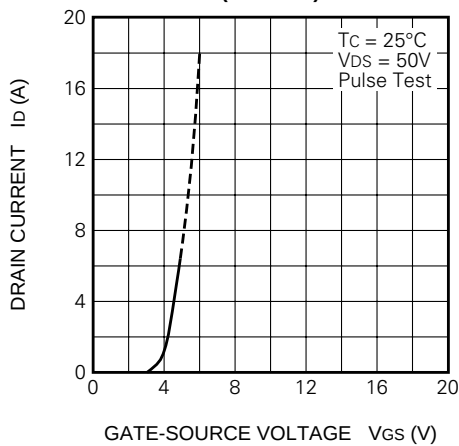
ON-STATE VOLTAGE VS.
GATE-SOURCE VOLTAGE
(TYPICAL)



ON-STATE RESISTANCE VS.
DRAIN CURRENT
(TYPICAL)



TRANSFER CHARACTERISTICS
(TYPICAL)



FORWARD TRANSFER ADMITTANCE
VS. DRAIN CURRENT
(TYPICAL)

